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WHAT IS CLAIMED IS:

1. A semiconductor laser device comprising:
 - a heat radiating block;
 - one or more first semiconductor laser element(s)5 arranged on said heat radiating block in a manner where one electrode is in contact therewith; and
 - one or more second semiconductor laser element(s) arranged on said heat radiating block in an electrically insulated manner via a dielectric layer.
- 10 2. The semiconductor laser device as set forth in Claim 1, wherein said first and second semiconductor laser elements are both integrated into one chip, and one electrode of the first semiconductor laser element is in contact with said 15 block, and the second semiconductor laser element is provided on said dielectric layer.
- 15 3. The semiconductor laser device as set forth in Claim 1, wherein said heat radiating block is an electrical conductor 20 or a semiconductor.
- 20 4. The semiconductor laser device as set forth in Claim 2, wherein said heat radiating block is an electrical conductor or a semiconductor.
- 25 5. The semiconductor laser device as set forth in Claim 1, comprising:
 - a light output monitoring photodiode built onto said heat radiating block.

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6. The semiconductor laser device as set forth in
Claim 2, comprising:

a light output monitoring photodiode built onto said
heat radiating block.

5 7. The semiconductor laser device as set forth in
Claim 3, comprising:

a light output monitoring photodiode built onto said
heat radiating block.

8. The semiconductor laser device as set forth in
10 Claim 1, wherein

said dielectric layer is formed of one selected from a
group consisting of silicon oxide, silicon nitride, titanium
oxide, aluminum oxide, and aluminum nitride.

9. The semiconductor laser device as set forth in
15 Claim 2, wherein

said dielectric layer is formed of one selected from a
group consisting of silicon oxide, silicon nitride, titanium
oxide, aluminum oxide, and aluminum nitride.

10. The semiconductor laser device as set forth in
20 Claim 3, wherein

said dielectric layer is formed of one selected from a
group consisting of silicon oxide, silicon nitride, titanium
oxide, aluminum oxide, and aluminum nitride.

11. The semiconductor laser device as set forth in
25 Claim 1, wherein

said first semiconductor laser element is greater in
heat generation during driving or smaller in heat radiation
from an element exposed surface than said second

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semiconductor laser element.

12. The semiconductor laser device as set forth in
Claim 2, wherein

said first semiconductor laser element is greater in
5 heat generation during driving or smaller in heat radiation
from an element exposed surface than said second
semiconductor laser element.

13. The semiconductor laser device as set forth in
Claim 3, wherein

10 said first semiconductor laser element is greater in
heat generation during driving or smaller in heat radiation
from an element exposed surface than said second
semiconductor laser element.

14. The semiconductor laser device as set forth in
15 Claim 1, wherein

said first semiconductor laser element is a
semiconductor laser to emit a laser beam with a 650nm-band
wavelength, and said second semiconductor laser element is a
semiconductor laser to emit a laser beam with a 780nm-band
20 wavelength.

15. The semiconductor laser device as set forth in
Claim 2, wherein

said first semiconductor laser element is a
semiconductor laser to emit a laser beam with a 650nm-band
25 wavelength, and said second semiconductor laser element is a
semiconductor laser to emit a laser beam with a 780nm-band
wavelength.

16. The semiconductor laser device as set forth in

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Claim 3, wherein

said first semiconductor laser element is a
semiconductor laser to emit a laser beam with a 650nm-band
wavelength, and said second semiconductor laser element is a
5 semiconductor laser to emit a laser beam with a 780nm-band
wavelength.